

加急出货

PU3117, PU4117, PU4417

Package Dimensions

Silicon NPN Triple-Diffused Planar Type

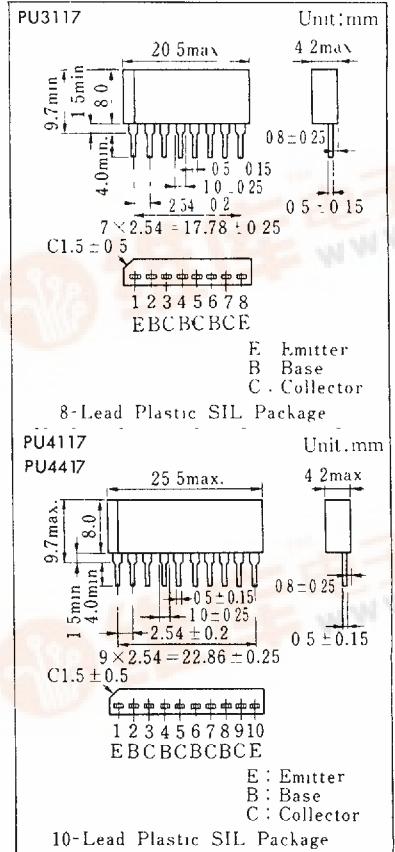
Power Amplifier, Switching

Features

- High DC current gain (h_{FE})
- Good linearity of DC current gain (h_{FE})
- PU3117: 3 NPN elements
- PU4117: 4 NPN elements
- PU4417: 2 NPN elements \times 2 (4 elements in total)

Absolute Maximum Ratings ($T_c=25^\circ\text{C}$)

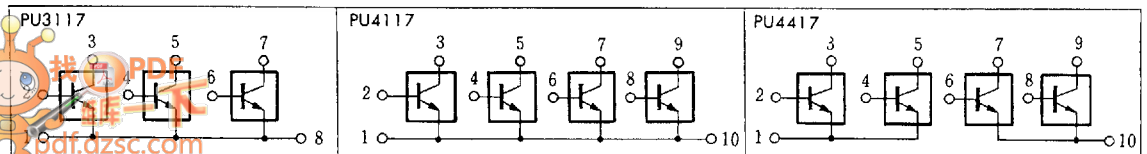
Item	Symbol	Value	Unit
Collector-base voltage	V_{CB0}	80	V
Collector-emitter voltage	V_{CE0}	60	V
Emitter-base voltage	V_{EB0}	6	V
Peak collector current	I_{CP}	6	A
Collector current	I_C	3	A
Base current	I_B	1	A
Power dissipation	P_D	15	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 ~ +150	$^\circ\text{C}$



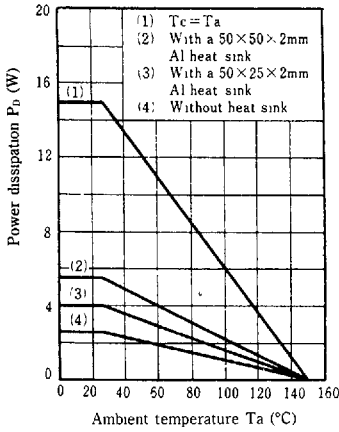
Electrical Characteristics ($T_c=25^\circ\text{C}$)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 80\text{V}, I_B = 0$			100	μA
	I_{CEO}	$V_{CE} = 40\text{V}, I_B = 0$			100	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = 6\text{V}, I_C = 0$			100	μA
Collector-emitter voltage	V_{CE0}	$I_C = 25\text{mA}, I_B = 0$	60			V
DC current gain	h_{FE}	$V_{CE} = 4\text{V}, I_C = 0.5\text{A}$	500		2500	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 2\text{A}, I_B = 0.05\text{A}$			1	V
Transition frequency	f_T	$V_{CE} = 12\text{V}, I_C = 0.2\text{A}, f = 10\text{MHz}$		50		MHz

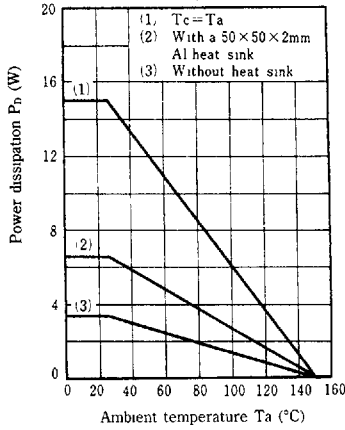
Inner Circuit



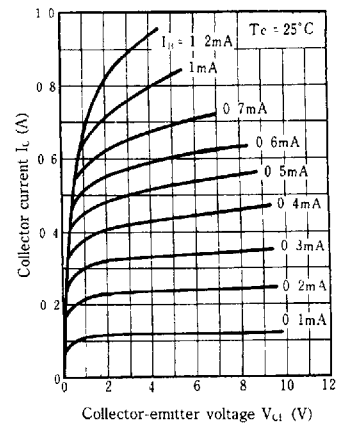
$P_D - T_a$ (PU3117)



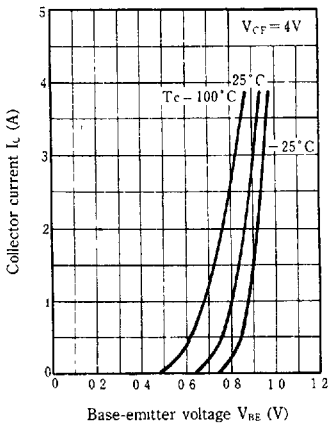
$P_D - T_a$ (PU4117, PU4417)



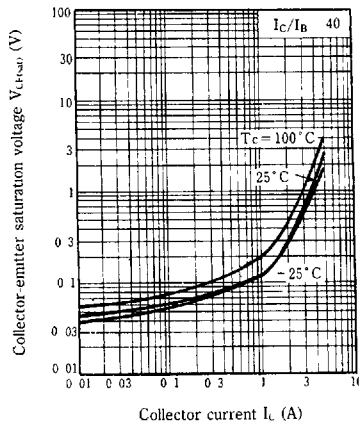
$I_C - V_{CE}$



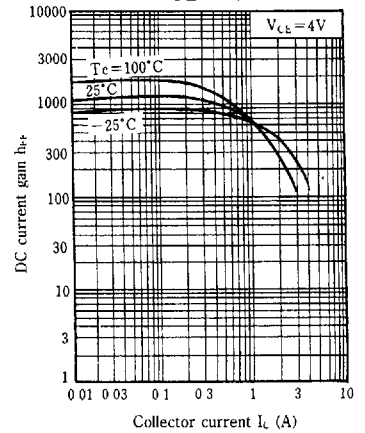
$I_C - V_{BE}$



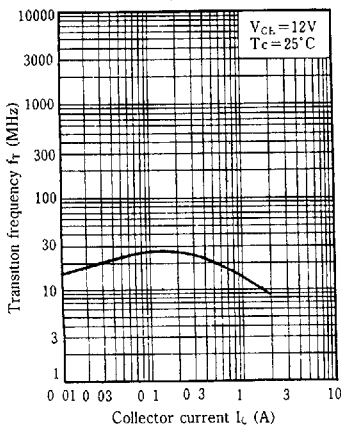
$V_{CE(sat)} - I_C$



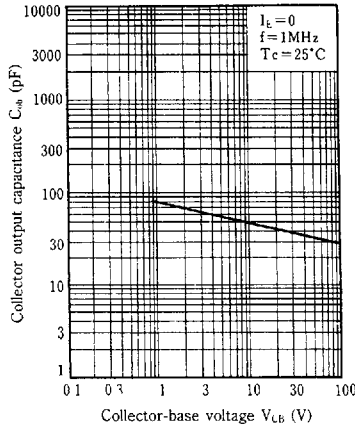
$h_{FE} - I_C$



$f_T - I_C$



$C_{ob} - V_{CB}$



Area of safe operation (ASO)

